

## N-channel 650 V, 0.087 $\Omega$ typ., 32 A MDmesh™ M2 Power MOSFET in I<sup>2</sup>PAK and TO-220 packages

Datasheet - production data

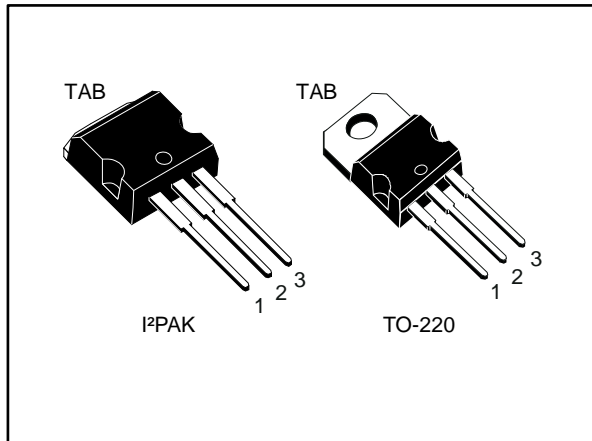


Figure 1: Internal schematic diagram

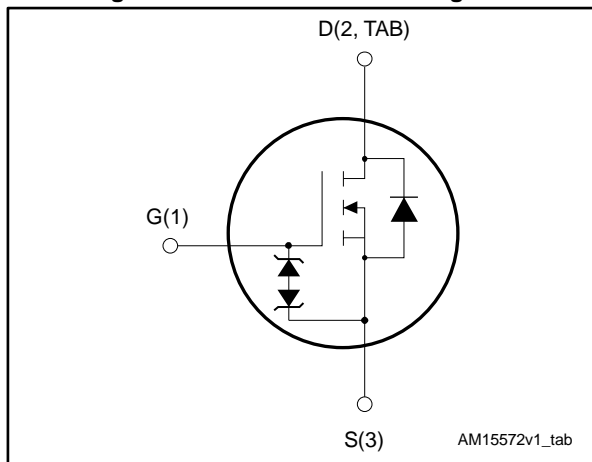


Table 1: Device summary

Order code	Marking	Package	Packaging
STI40N65M2	40N65M2	I <sup>2</sup> PAK	Tube
STP40N65M2		TO-220	

### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STI40N65M2	650 V	0.099 $\Omega$	32 A
STP40N65M2			

- Extremely low gate charge
- Excellent output capacitance (C<sub>oss</sub>) profile
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

These devices are N-channel Power MOSFETs developed using MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, the devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high efficiency converters.

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	32	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	20	A
$I_{DM}^{(1)}$	Drain current (pulsed)	128	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	250	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	°C
$T_j$	Max. operating junction temperature	150	

**Notes:**

<sup>(1)</sup> Pulse width limited by safe operating area.

<sup>(2)</sup>  $I_{SD} \leq 32\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$

<sup>(3)</sup>  $V_{DS} \leq 520\text{ V}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.50	°C/W

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	3	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	820	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5: On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	650			V
$I_{DSS}$	Zero gate voltage Drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 650\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 650\text{ V}$ , $T_C = 125\text{ °C}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$		0.087	0.099	$\Omega$

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	2355	-	pF
$C_{oss}$	Output capacitance		-	102	-	pF
$C_{rss}$	Reverse transfer capacitance		-	2.7	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ V to } 520\text{ V}$ , $V_{GS} = 0\text{ V}$	-	380	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , open drain	-	4.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 32\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15: "Gate charge test circuit"</a> )	-	56.5	-	nC
$Q_{gs}$	Gate-source charge		-	8	-	nC
$Q_{gd}$	Gate-drain charge		-	24	-	nC

**Notes:**

<sup>(1)</sup> $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$ , $I_D = 16\text{ A}$ $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14: "Switching times test circuit for resistive load"</a> and <a href="#">Figure 19: "Switching time waveform"</a> )	-	15	-	ns
$t_r$	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off-delay time		-	96.5	-	ns
$t_f$	Fall time		-	12	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		32	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		128	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 32\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 32\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 16</a> : " <i>Test circuit for inductive load switching and diode recovery times</i> ")	-	468		ns
$Q_{rr}$	Reverse recovery charge		-	8.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	37.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 32\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 16</a> : " <i>Test circuit for inductive load switching and diode recovery times</i> ")	-	610		ns
$Q_{rr}$	Reverse recovery charge		-	11.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	39		A

**Notes:**

<sup>(1)</sup> Pulse width is limited by safe operating area

<sup>(2)</sup> Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.2 Electrical characteristics (curves)

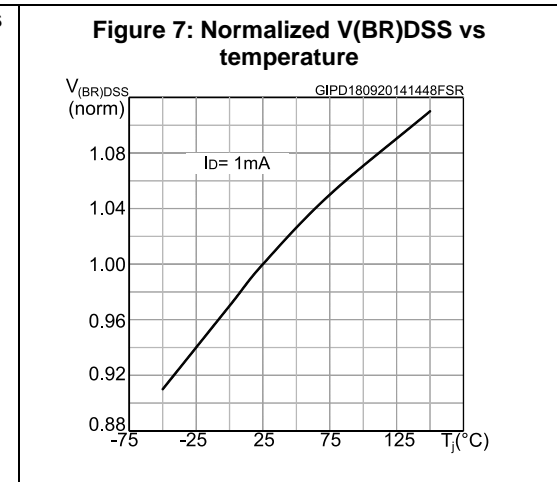
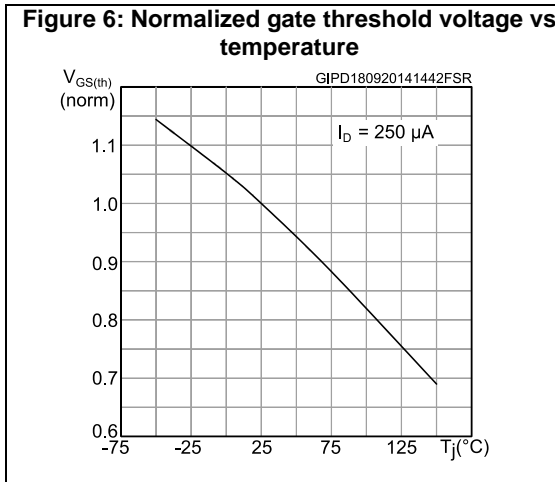
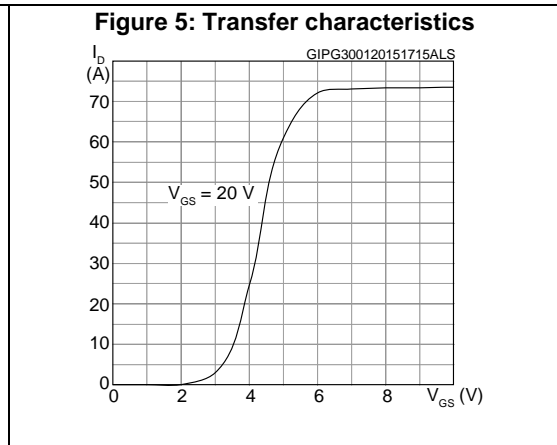
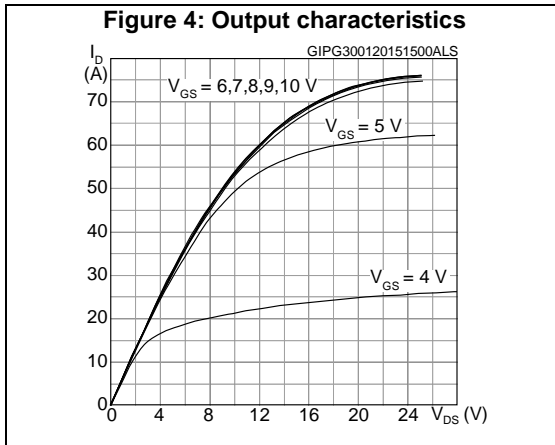
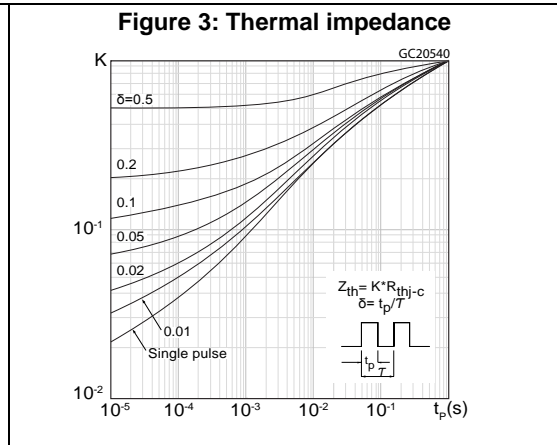
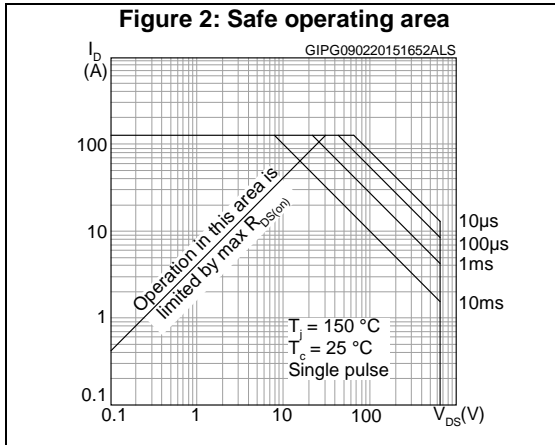


Figure 8: Static drain-source on-resistance

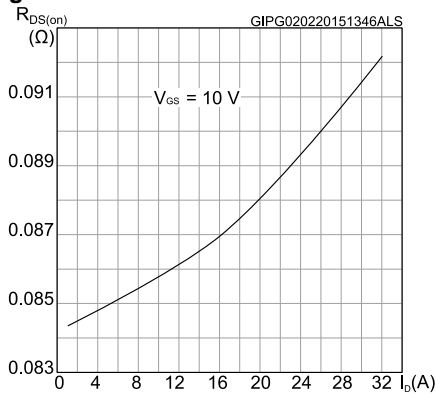


Figure 9: Normalized on-resistance vs. temperature

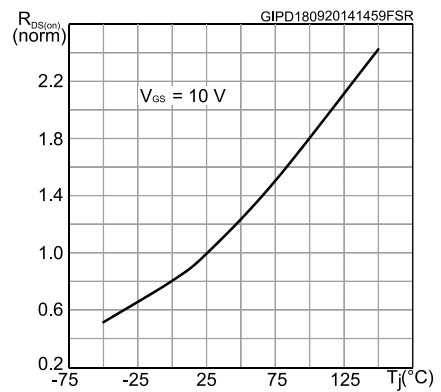


Figure 10: Gate charge vs. gate-source voltage

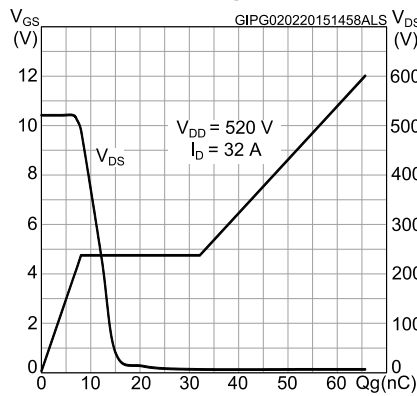


Figure 11: Capacitance variations

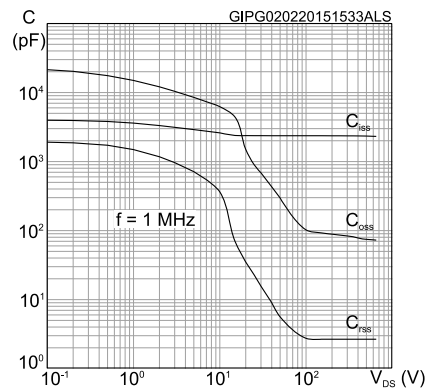


Figure 12: Output capacitance stored energy

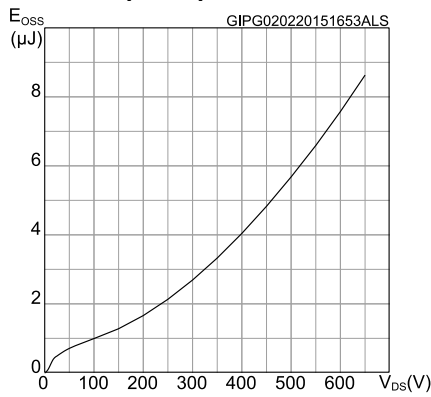
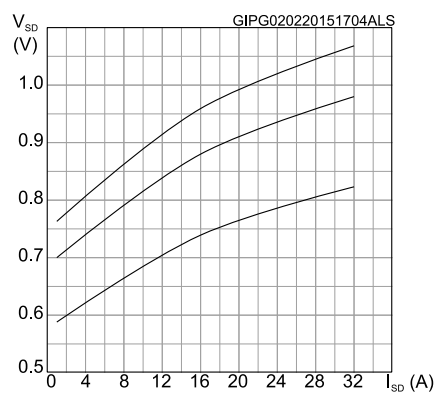
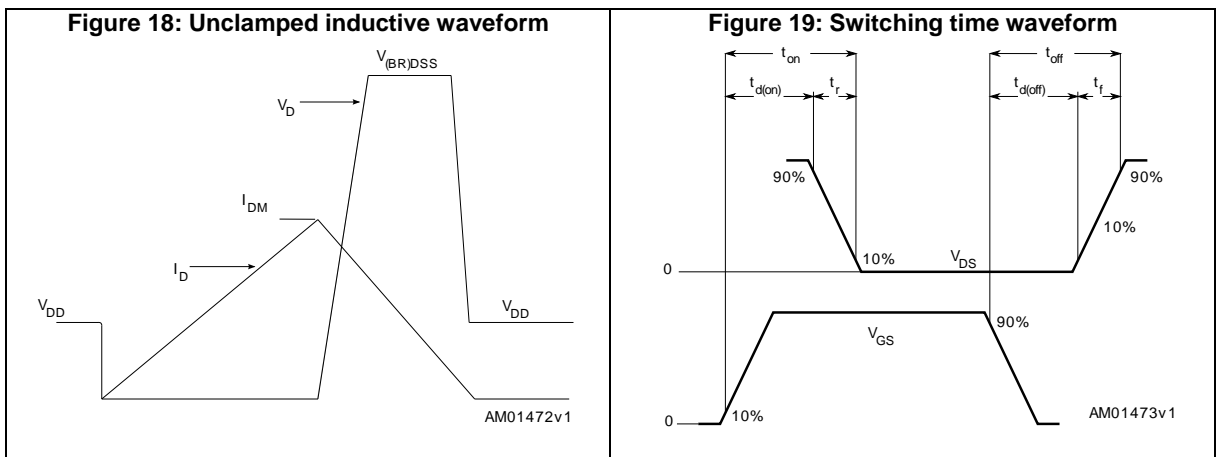
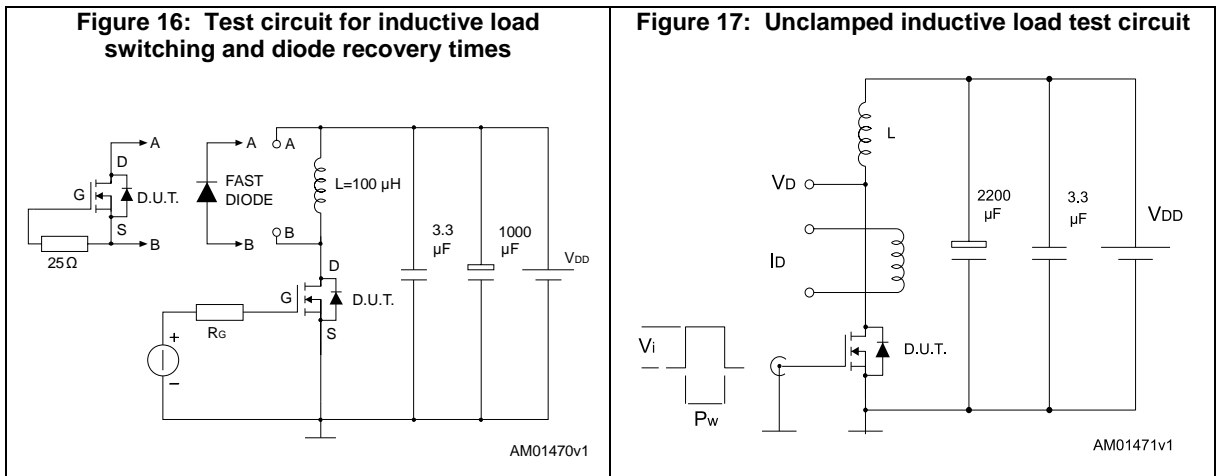
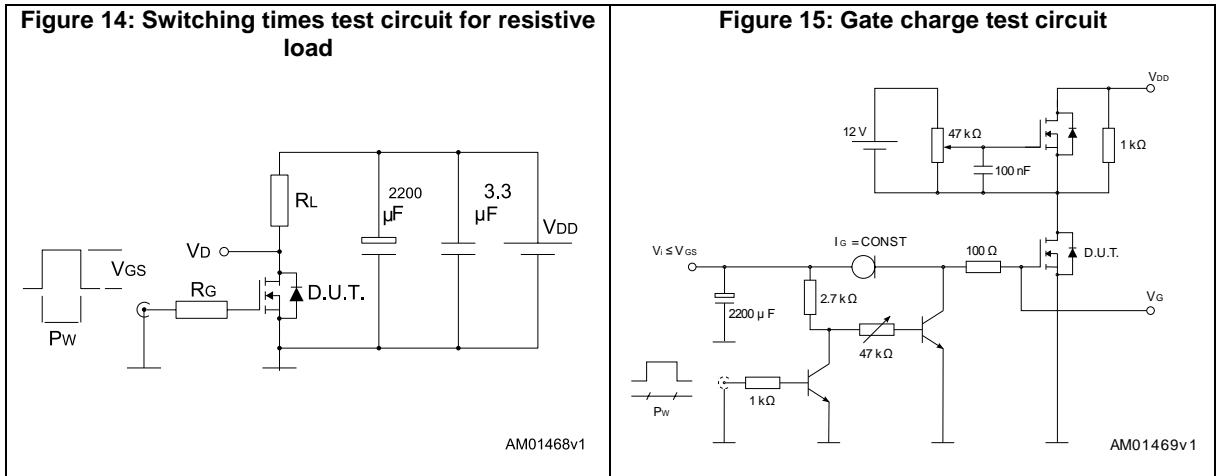


Figure 13: Source-drain diode forward characteristics



### 3 Test circuits





## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 I<sup>2</sup>PAK package information

Figure 20: I<sup>2</sup>PAK package outline

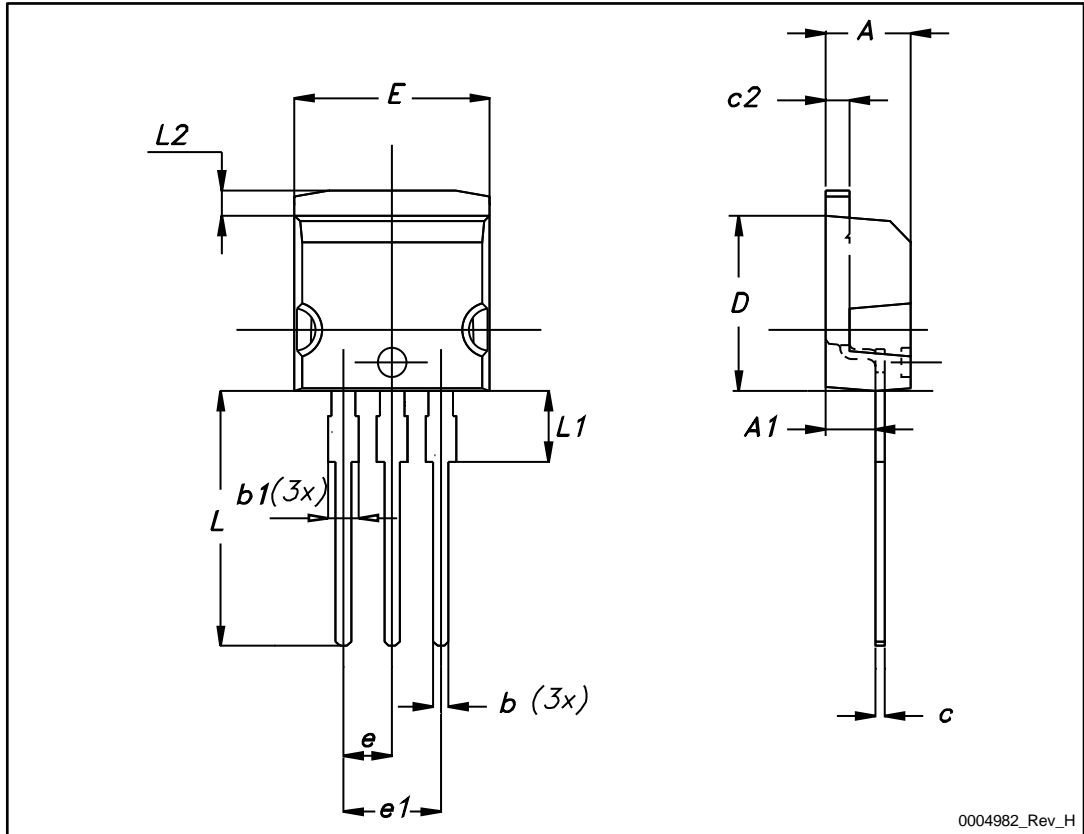
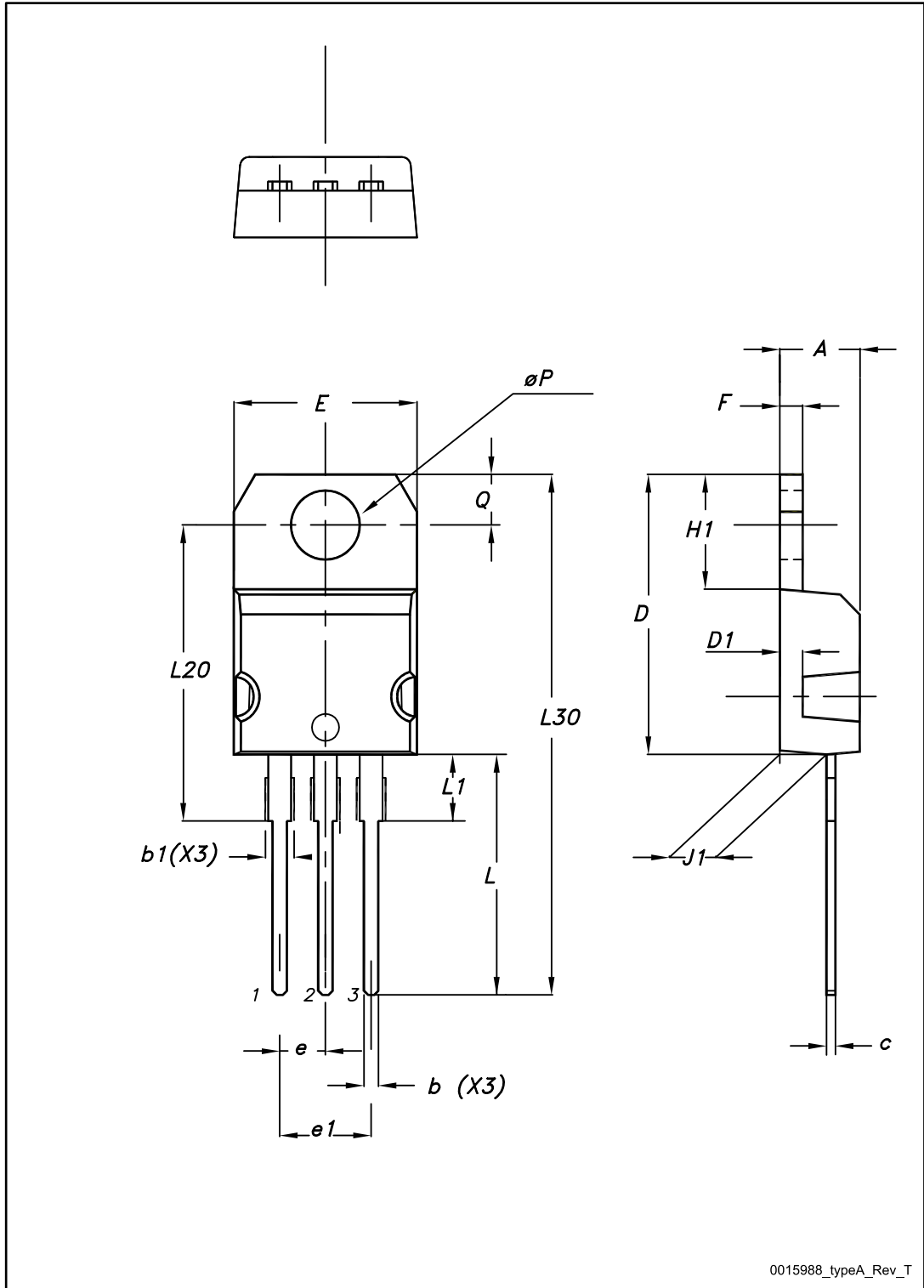


Table 9: I<sup>2</sup>PAK mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40	–	4.60
A1	2.40	–	2.72
b	0.61	–	0.88
b1	1.14	–	1.70
c	0.49	–	0.70
c2	1.23	–	1.32
D	8.95	–	9.35
e	2.40	–	2.70
e1	4.95	–	5.15
E	10	–	10.40
L	13	–	14
L1	3.50	–	3.93
L2	1.27	–	1.40

### 4.2 TO-220 type A package information

Figure 21: TO-220 type A package outline



0015988\_typeA\_Rev\_T

Table 10: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

## 5 Revision history

Table 11: Document revision history

Date	Revision	Changes
09-Feb-2014	1	First release.

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